

Abstracts

Performance and Reliability of K_{sub a}-Band GaAs IMPATT Diodes

R.A. Murphy, W.T. Lindley, D.F. Peterson and P. Staecker. "Performance and Reliability of K_{sub a}-Band GaAs IMPATT Diodes." 1974 S-MTT International Microwave Symposium Digest of Technical Papers 74.1 (1974 [MWSYM]): 315-317.

K_{sub a}-band GaAs p-n junction IMPATT diodes have been fabricated which have delivered 450 mW of added power with 9.6% efficiency at a junction temperature of 275°C. Results of life tests predict operating life in excess of five years at this temperature.

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